

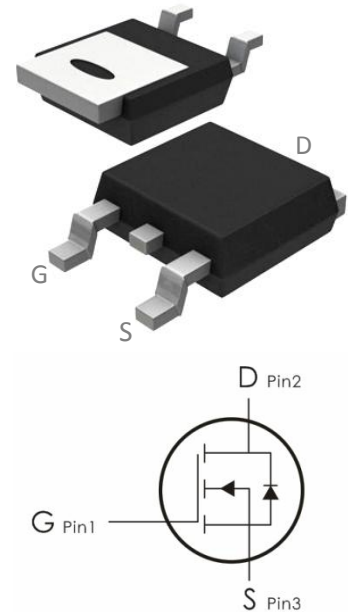
Description:

This N-Channel MOSFET uses advanced trench technology and design to provide excellent $R_{DS(on)}$ with low gate charge.

It can be used in a wide variety of applications.

Features:

- 1) $V_{DS}=20V, I_D=60A, R_{DS(on)} < 6.5m\Omega @ V_{GS}=4.5V$
- 2) Low gate charge.
- 3) Green device available.
- 4) Advanced high cell density trench technology for ultra low $R_{DS(on)}$.
- 5) Excellent package for good heat dissipation.



Absolute Maximum Ratings: ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Ratings	Units
V_{DS}	Drain-Source Voltage	20	V
V_{GS}	Gate-Source Voltage	± 12	V
I_D	Continuous Drain Current- $T_C=25^\circ C$	60	A
	Continuous Drain Current- $T_C=100^\circ C$	39	A
I_{DM}	Pulsed Drain Current ¹	240	A
P_D	Power Dissipation	37	W
E_{AS}	Single pulse avalanche energy ²	47.6	mJ
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	$^\circ C$
$R_{\theta JC}$	Thermal Resistance, Junction to Case	4	$^\circ C/W$

Package Marking and Ordering Information:

Part NO.	Marking	Package
DB006NG-B	B006N-B	TO-252

Electrical Characteristics: ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Sourctce Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	20	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =20V, V _{GS} =0V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ± 12V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	GATE-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	0.4	0.7	1	V
R _{DS(ON)}	Drain-Source On Resistanc ³	V _{GS} =4.5V, I _D =25A	---	4.8	6.5	m Ω
		V _{GS} =2.5V, I _D =15A	---	6.8	10	m Ω
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	---	1831	---	pF
C _{oss}	Output Capacitance		---	288	---	
C _{rss}	Reverse Transfer Capacitance		---	270	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	VDD=10V R _{GEN} =3Ω , I _D =25A	---	14	---	ns
t _r	Rise Time		---	36	---	ns
t _{d(off)}	Turn-Off Delay Time		---	51	---	ns
t _f	Fall Time		---	20	---	ns
Q _g	Total Gate Charge	V _{GS} =4.5V, V _{DS} =10V, I _D =25A	---	22	---	nC
Q _{gs}	Gate-Source Charge		---	4.4	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	7.2	---	nC
Drain-Source Diode Characteristics						
I _S	Continuous Source Current	VG=VD=0V	---	---	60	A
I _{SM}	Pulsed Drain Current	VG=VD=0V	---	---	240	A
V _{SD}	Diode Forward Voltage ²	V _{GS} =0V , I _D =30A	---	---	1.2	V
T _{rr}	Reverse Recovery Time	IF=25A , dI/dt=100A/μs ,	---	25	---	ns
Q _{rr}	Reverse Recovery Charge		---	21	---	nC

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition: $T_J=25^{\circ}\text{C}$, $V_{DD}=10\text{V}$, $V_G=4.5\text{V}$, $L=0.5\text{mH}$, $R_G=25\Omega$, $I_{AS}=13.8\text{A}$
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$

Typical Characteristics:

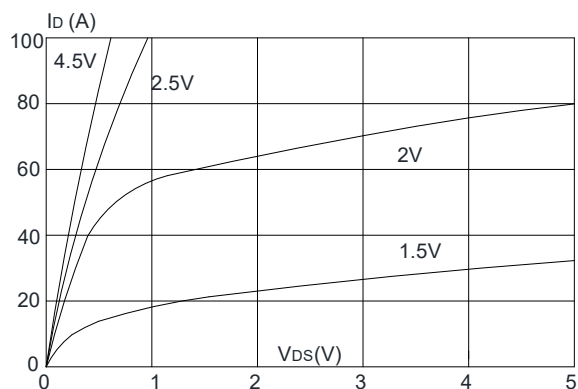


Figure 1: Output Characteristics

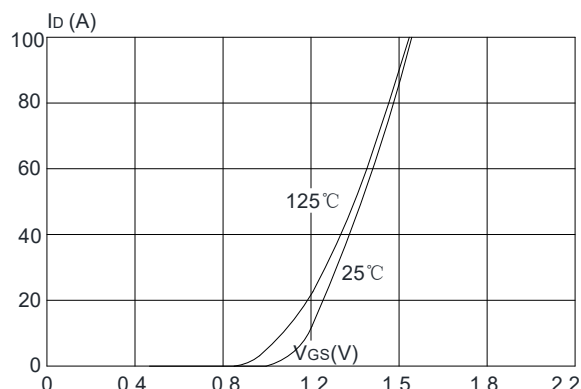


Figure 2: Typical Transfer Characteristics

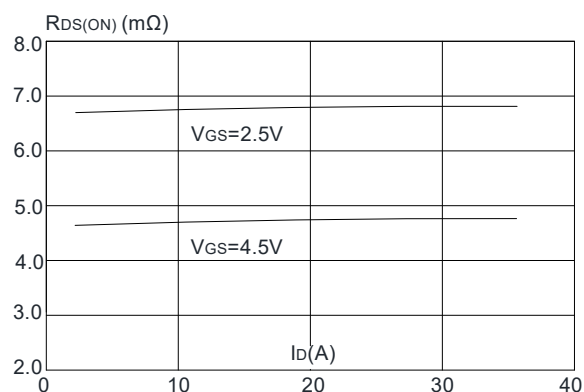


Figure 3: On-resistance vs. Drain Current

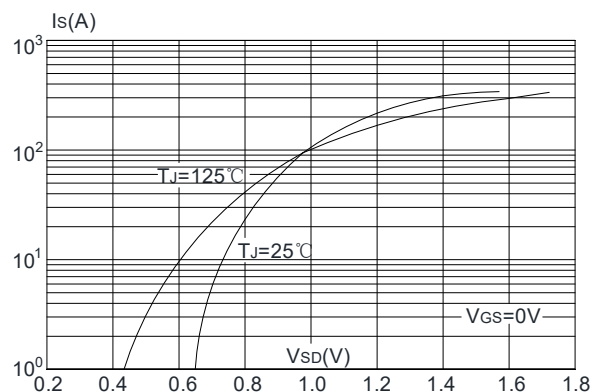


Figure 4: Body Diode Characteristics

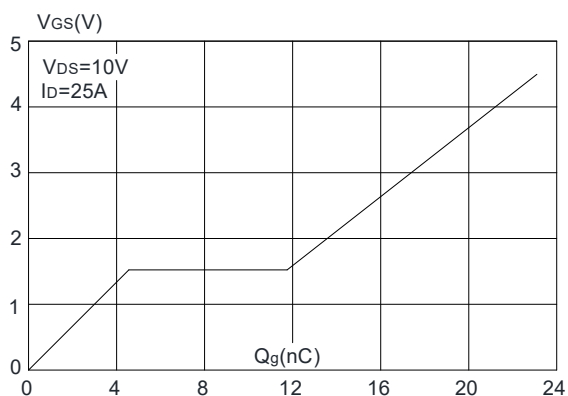


Figure 5: Gate Charge Characteristics

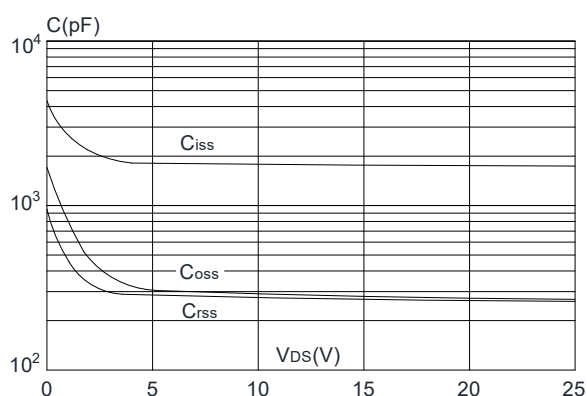


Figure 6: Capacitance Characteristics

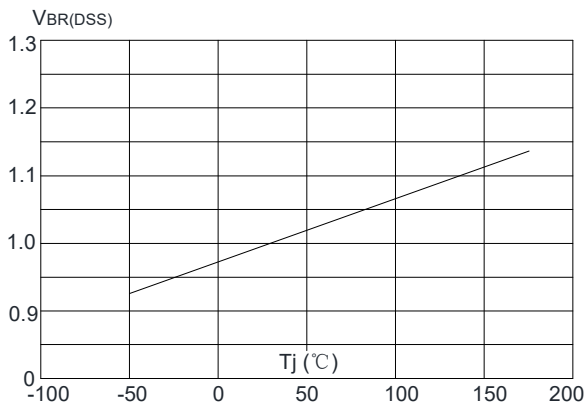


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

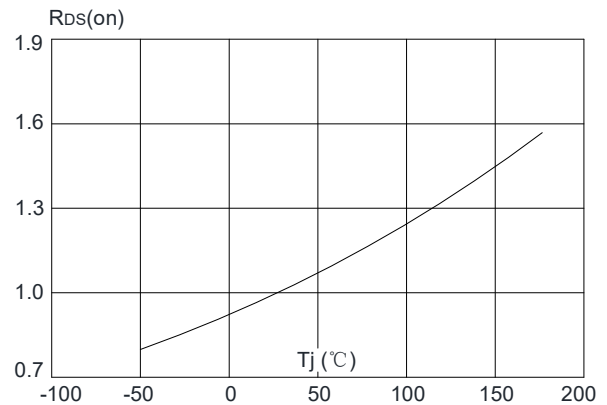


Figure 8: Normalized on Resistance vs. Junction Temperature

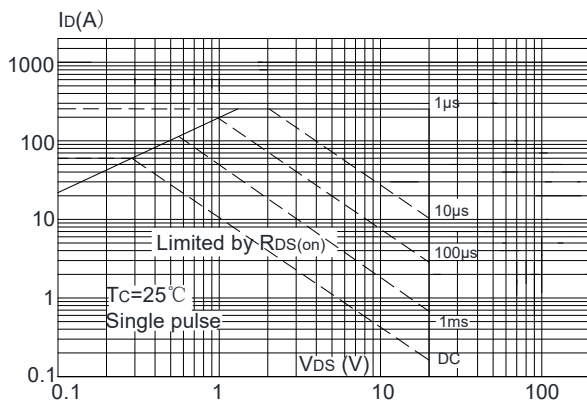


Figure 9: Maximum Safe Operating Area

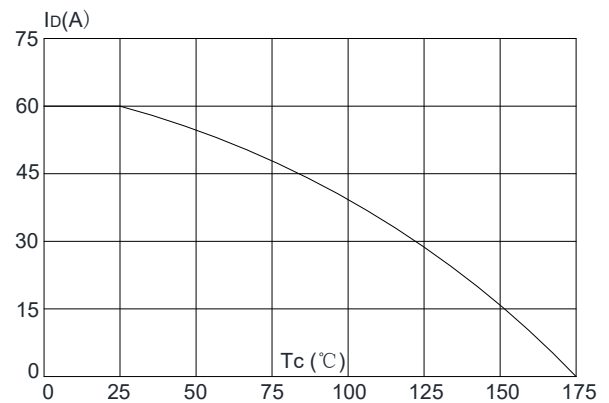


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

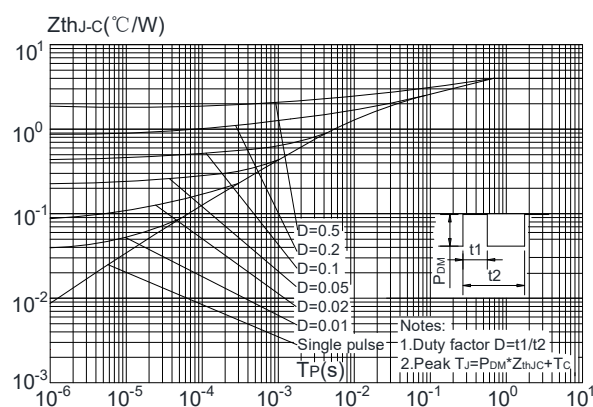


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case